

DALLAS SEMICONDUCTOR IME

Goal = 300 ppm

Flow	Part	IME Results											
		3Q03			2Q03			1Q03			4Q02		
		Total	Fails	PPM	Total	Fails	PPM	Total	Fails	PPM	Total	Fails	PPM
D6E	DS4000												
D6H	DS1050												
D6H	DS21352												
D6H	DS21554												
D6H	DS2196												
D6L	DS7864B				3277	3	915						
D6N	DS12885												
D6N	DS1643												
D6RH	DS5240												
D6RL	DS80C320												
D6RL	DS80CH11												
D6S	DS2118M	3332	0	0							3286	0	0
D6W	DS1848												
D6W	DS1849				2696	7	2596						
D6W	DS1859				3089	1	324						
D8ET	DS87C520												
D8G	DS1780												
D8N	DS17885										7190	70	9736
D8R-N	DS2154												
D8S	DS1232												
D8S	DS1834				2534	1	395						
D8S	DS21T07												
D8W	DS1621												
E6H	DS21354	3372	3	890									
E6S	DS2118M	9248	3	324	17116	10	584						

Dallas fab qualified processes only.
 Dates are by calendar year, not fiscal year.
 Data is grouped by fab lot starting quarter.
 IME is B/I 12 hours at 125C and max. op. volt.